



Docket No.: 50088-057

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Masami SHIROSAKI, et al.

Serial No.: 09/833,734

Filed: April 13, 2001

For: SEMICONDUCTOR DEVICE AND METHOD FOR PRODUCING A
SEMICONDUCTOR DEVICE

Group Art Unit: 2823

Examiner: Julio J. Maldonado

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AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office
Action dated August 20, 2002.

IN THE SPECIFICATION:

Please amend the paragraph beginning at page 15, line 23 as follows:

As shown in Figure 3, the amorphous silicon film [13b] 13a remains without

discontinuation in the inner wall of the cylindrical portion 6d, and surface of the

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01 FC:1201 amorphous silicon film [13b] 13a is smooth. The remaining amorphous silicon film

[13b] 13a is sufficient to keep the physical strength of the cylindrical portion 6b even

after the formation of the silicon grains 13b.

Please amend the paragraph beginning at page 19, line 18 as follows: